



**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**In re Reissue Application of:**

Dennison et al.

**U.S. Patent No.:** 5,229,326

**Issued:** July 20, 1993

**For:** METHOD FOR MAKING ELECTRICAL  
CONTACT WITH AN ACTIVE AREA  
THROUGH SUB-MICRON CONTACT  
OPENINGS AND A SEMICONDUCTOR  
DEVICE

**Reissue Serial No.:** 09/488,099

**Filed:** January 18, 2000

**Examiner:** K. Picardat

**Group Art Unit:** 2822

**Attorney Docket No.:** 3255.1US (91-507.1-  
RE)

**CERTIFICATE OF MAILING**

I hereby certify that this paper or fee along with any attachments referred to or identified as being attached or enclosed is being deposited with the United States Postal Service as First Class Mail (under 37 C.F.R. § 1.8(a)) on the date of deposit shown below with sufficient postage and in an envelope addressed to the Commissioner for Patents, Washington, D.C. 20231.

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1.8(a)(1)(ii)

Joseph A. Walkowski  
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**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In compliance with the duty to disclose information material to patentability pursuant to 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed on attached Form PTO-1449 or PTO/SB/08A be considered by the Examiner and made of record. Copies of the listed documents are enclosed pursuant to 37 C.F.R. § 1.98(a).

In accordance with 37 C.F.R. § 1.97(g) and (h), filing of this Information Disclosure Statement is not to be construed as a representation that a search has been made or an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b). Further, no representation is made by Applicants herein that no other possible material information as defined in 37 C.F.R. § 1.56 (b) exists.

### DOCUMENTS

#### U.S. Patent Documents

<u>U.S. Patent No.</u>	<u>Issue Date</u>	<u>Inventor</u>
4,617,193	10/1986	Wu
4,714,686	12/1987	Sander et al.
4,868,138	09/1989	Chan et al.
4,892,845	01/1990	Bridges
5,110,766	05/1992	Maeda et al.
5,124,280	06/1992	Wei et al.
5,158,910	10/1992	Cooper et al.
5,171,713	12/1992	Matthews

#### Foreign Patent Documents

<u>Document No.</u>	<u>Date</u>	<u>Country</u>
41 07 883	09/1991	DE
62-32630	02/1987	JP
64-72543	03/1989	JP

#### Other Documents

Yoshire Nakata et al., "Tunnel Shape Stacked Capacitor (TSSC) Memory Cell for 64Mb Dram", article (date unknown).



Application Serial No. 09/488,099

Applicants offer to supply any explanation or discussion of the documents which the Examiner feels is necessary or desirable and which is requested.

This Information Disclosure Statement is filed after the mailing date of the first Office Action on the merits. The fee pursuant to 37 C.F.R. § 1.17(p) is enclosed.

Respectfully submitted,

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Date: April 5, 2002

JAW/ps:dlm

Enclosures: Form PTO-1449 or PTO/SB/08A  
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Sheet 1 of 1

Form PTO-1449 <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> <i>(Use several sheets if necessary)</i>	Docket Number (Optional) <b>3255.1US (91-507.1-RE)</b>	Application Number <b>09/488,099</b>
	Applicant <b>Dennison et al.</b>	
	Filing Date <b>January 18, 2000</b>	Group Art Unit <b>2822</b>

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,617,193	10/1986	Wu			
	4,714,686	12/1987	Sander et al.			
	4,868,138	09/1989	Chan et al.			
	4,892,845	01/1990	Bridges			
	5,110,766	05/1992	Maeda et al.			
	5,124,280	06/1992	Wei et al.			
	5,158,910	10/1992	Cooper et al.			
	5,171,713	12/1992	Matthews			

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	41 07 883	09/1991	DE			X	
	62-32630	02/1987	JP			X	
	64-72543	03/1989	JP			X	

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

		Yoshire Nakata et al., "Tunnel Shape Stacked Capacitor (TSSC) Memory Cell for 64Mb Dram", article (date unknown).
EXAMINER		DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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4/5/02